

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (MACHII π -MOSVI)

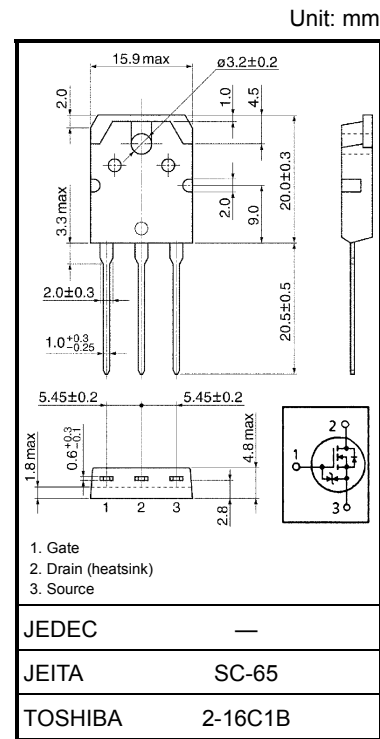
2SK3907

Switching Regulator Applications

- Small gate charge: $Q_g = 60 \text{ nC}$ (typ.)
- Low drain-source ON resistance: $R_{DS(ON)} = 0.18 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 12 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 500 \mu\text{A}$ ($V_{DS} = 500 \text{ V}$)
- Enhancement model: $V_{th} = 2.0\text{--}4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	500	V
Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)		V_{DGR}	500	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	23	A
	Pulse (Note 1)	I_{DP}	92	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	150	W
Single pulse avalanche energy (Note 2)		E_{AS}	552	mJ
Avalanche current		I_{AR}	23	A
Repetitive avalanche energy (Note 3)		E_{AR}	15	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~150	$^\circ\text{C}$



Weight: 4.6 g (typ.)

Thermal Characteristics

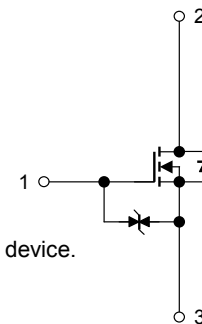
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.833	°C/W
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.

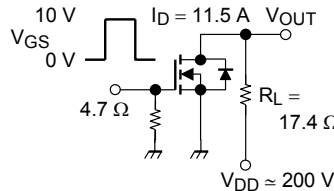
Note 2: $V_{DD} = 90\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.77\text{ mH}$, $I_{AR} = 23\text{ A}$, $R_G = 25\ \Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



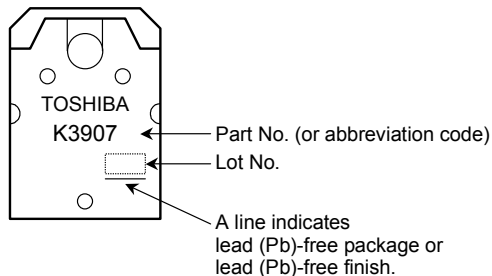
Electrical Characteristics (Ta = 25°C)

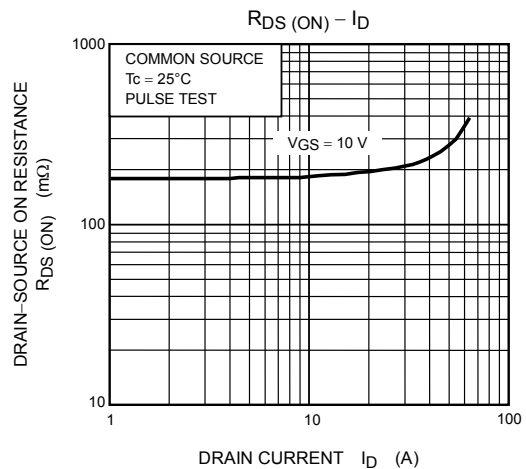
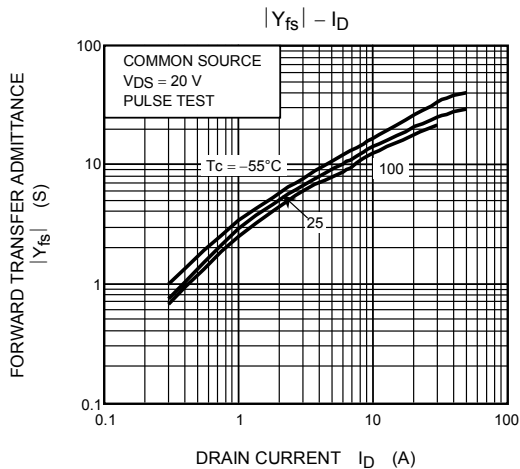
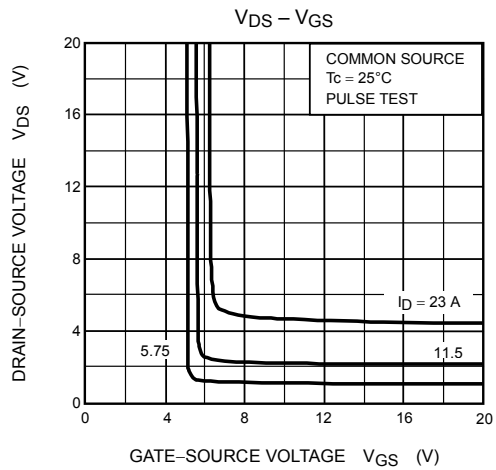
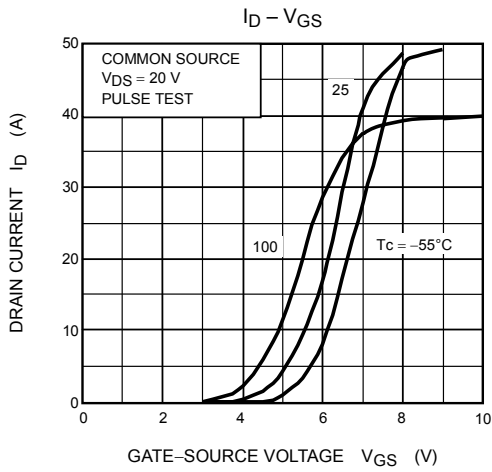
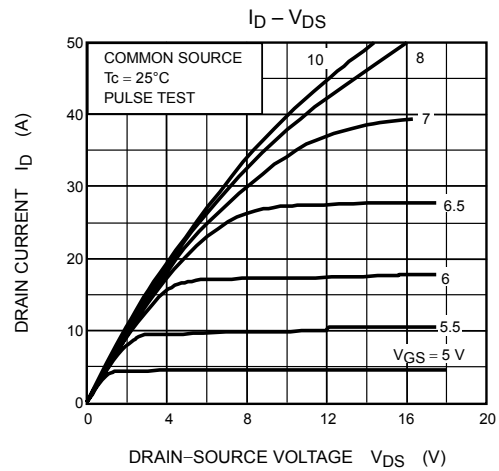
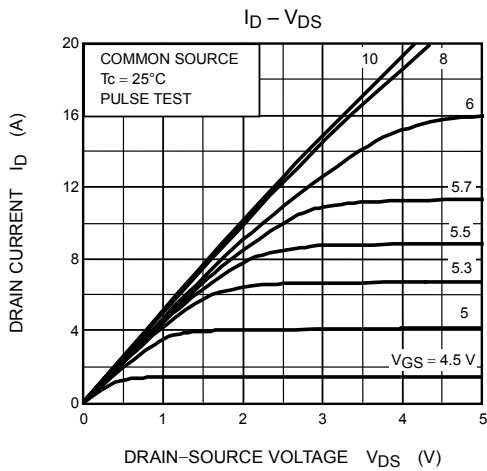
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_D = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cutoff current		I_{DSS}	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	500	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 11.5 \text{ A}$	—	0.18	0.23	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 11.5 \text{ A}$	3.4	12	—	S
Input capacitance		C_{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	4250	—	pF
Reverse transfer capacitance		C_{rss}		—	10	—	
Output capacitance		C_{oss}		—	420	—	
Switching time	Rise time	t_r		—	12	—	ns
	Turn-on time	t_{on}		—	45	—	
	Fall time	t_f		—	10	—	
	Turn-off time	t_{off}		—	80	—	
Total gate charge		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 23 \text{ A}$	—	60	—	nC
Gate-source charge		Q_{gs}		—	50	—	
Gate-drain charge		Q_{gd}		—	10	—	

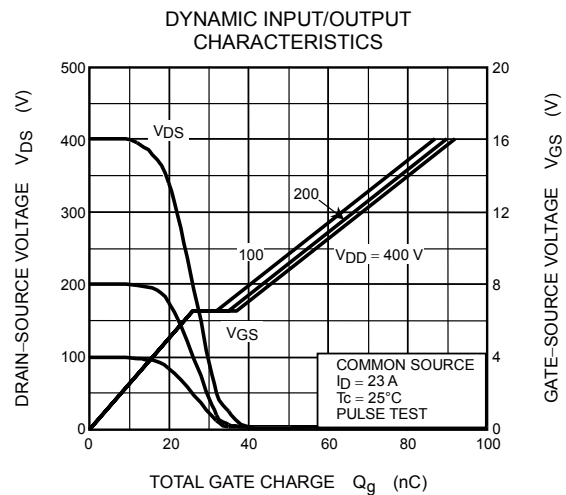
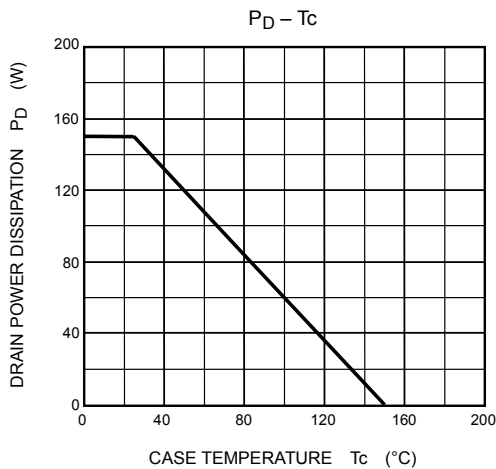
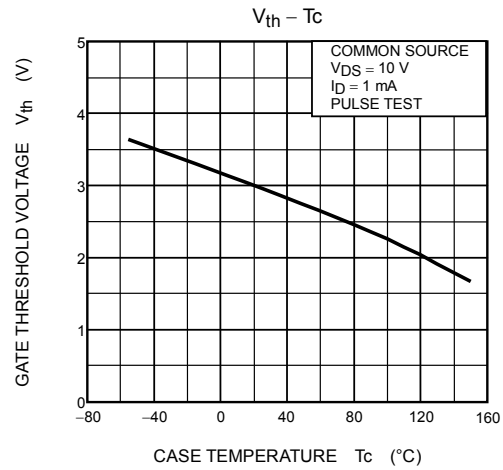
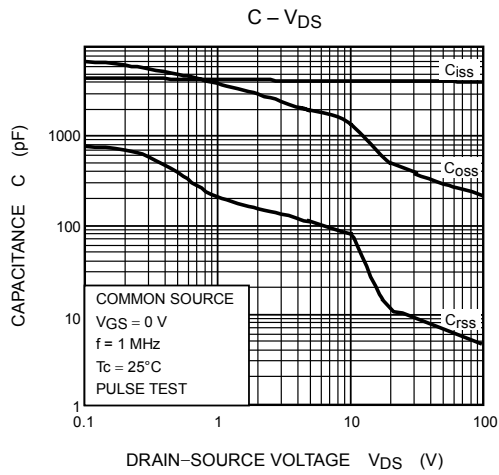
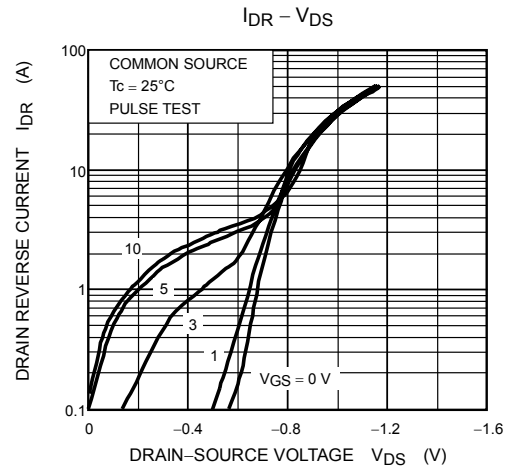
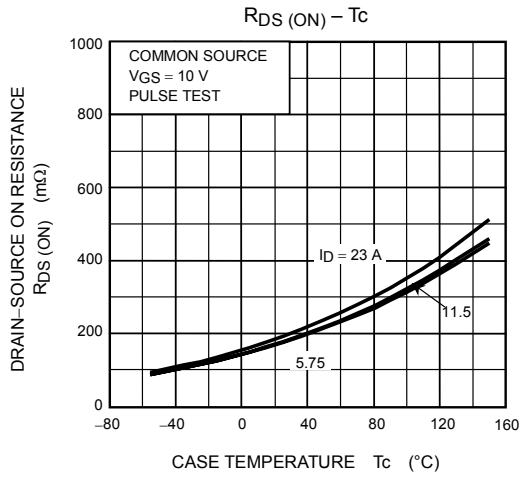
Source-Drain Ratings and Characteristics (Ta = 25°C)

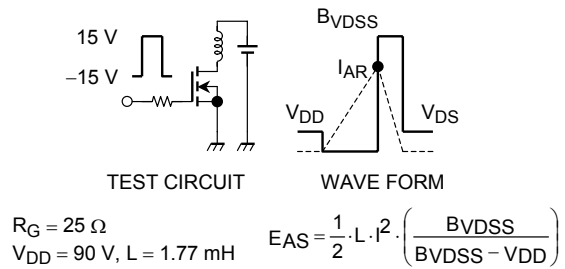
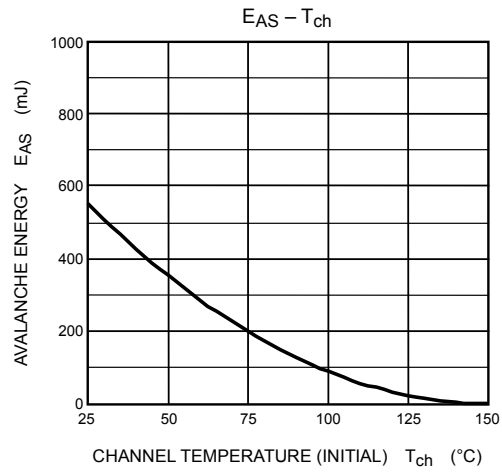
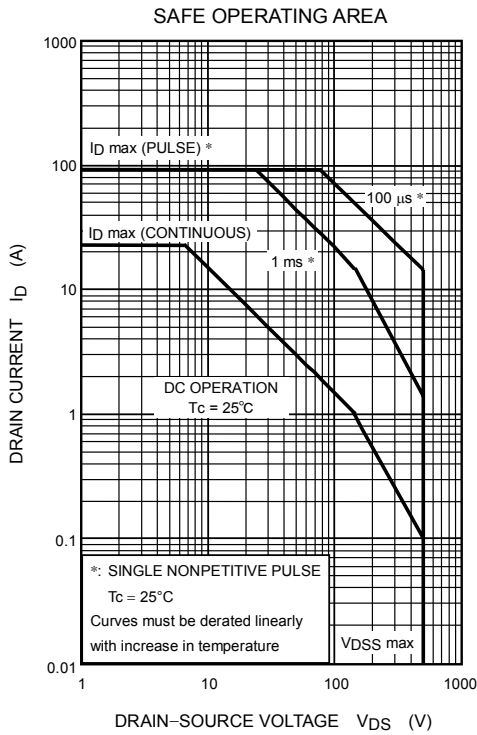
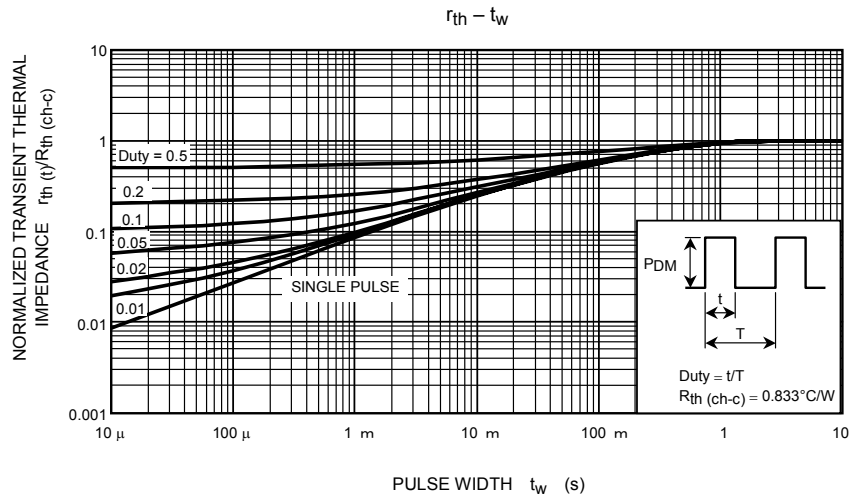
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	23	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	92	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 23 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 23 \text{ A}, V_{GS} = 0 \text{ V},$ $dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	1350	—	ns
Reverse recovery charge	Q_{rr}		—	24	—	μC

Marking









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